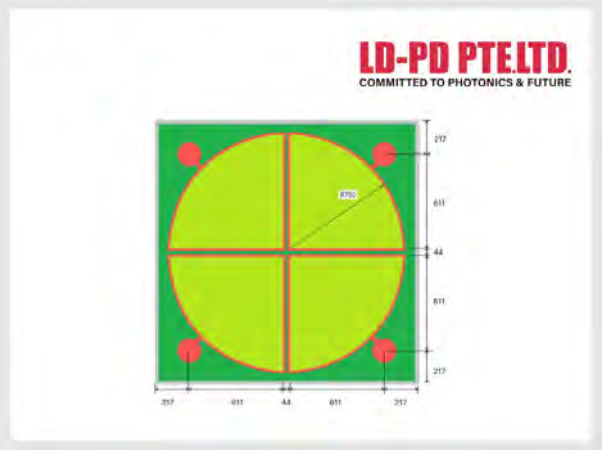
LP1500F4 InGaAs Four Quadrants Monitor PD Chip



Description

InGaAs Quadrant PIN Detector, high sensitivity photo-diode for use in infrared instrumentation and sensing applications. High spectral response in the region 800 nm to 1700 nm. The photosensitive area is 4x1.5mm in diameter. Planar-passivated device structure.

Features

- Φ1500nm active area
- High responsivity
- Low capacitance
- Low dark current
- Top illuminated planar structure

Parameters（Tc=25℃）

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Response range	λ	900		1650	nm	
Responsivity	R	0.85	0.90		A/W	λ= 1310nm
			0.95			λ= 1550nm
			0.2			λ=850nm

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Dark current	ID		5.0	15.0	nA	VR=-5V
Capacitance	C		100	150	pF	VR=-5V, f= 1MHz

Absolute Maximum Ratings

PARAMETER	SYMBOL	VALUE	UNIT
Reverse voltage	VRmax	20	V
Operating temperature	Topr	-40 to +85	°C
Storage temperature	Tstg	-55 to +125	°C

Dimension

PARAMETER	SYMBOL	VALUE	UNIT
Active area diameter	D	1500	μm
Bond pad diameter	-	150	μm
Die size	-	1700x1700	μm
Die thickness	t	180±20	μm

Precautions for use

This chip is susceptible to damage as a result of ESD. Use of ground straps, antistatic mats, and other standard ESD protective equipment is requisite when handling or testing an InGaAs or GaAs PIN/APD chip.

Application

- Beam Alignment
- Optical Tracking,Positioning
- Laser Position Monitor